**Preferred Device** 

# **Amplifier Transistors**

# **PNP Silicon**

#### **Features**

• Pb-Free Packages are Available\*



Rating	Symbol	2N5400	2N5401	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	120	150	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	130	160	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	5.0		Vdc
Collector Current – Continuous	I <sub>C</sub>	600		mAdc
Total Device Dissipation  @ T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	625 5.0		mW mW/°C
Total Device Dissipation  @ T <sub>C</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

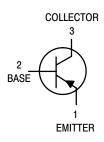
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	83.3	°C/W



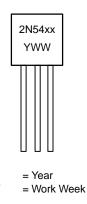
# ON Semiconductor®

#### http://onsemi.com





### **MARKING DIAGRAM**



#### **ORDERING INFORMATION**

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See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**Preferred** devices are recommended choices for future use and best overall value.

#### 2N5401

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•	
Collector-Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	2N5400 2N5401	V <sub>(BR)</sub> CEO	150	_	Vdc
Collector-Base Breakdown Voltage ( $I_C = 100 \mu Adc, I_E = 0$ )	2N5400 2N5401	V <sub>(BR)</sub> CBO	160	_	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ )		V <sub>(BR)EBO</sub>	5.0	_	Vdc
Collector Cutoff Current $(V_{CB} = 120 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 120 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	2N5401 2N5401	Ісво	- -	50 50	
Emitter Cutoff Current (V <sub>EB</sub> = 3.0 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	-	50	nAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain $ \begin{aligned} &(I_C=1.0 \text{ mAdc, V}_{CE}=5.0 \text{ Vdc)} \\ &(I_C=10 \text{ mAdc, V}_{CE}=5.0 \text{ Vdc)} \\ &(I_C=50 \text{ mAdc, V}_{CE}=5.0 \text{ Vdc)} \end{aligned} $		h <sub>FE</sub>	50 60 50	_ 240 _	_
Collector-Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )		V <sub>CE(sat)</sub>	- -	0.2 0.5	Vdc
Base – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )		V <sub>BE(sat)</sub>	- -	1.0 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc, f = 100 MHz)		f <sub>T</sub>	100	300	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	-	6.0	pF
Small–Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)		h <sub>fe</sub>	40	200	_
Noise Figure (I <sub>C</sub> = 250 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 k $\Omega$ , f =	1.0 kHz)	NF	-	8.0	dB

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%.$ 

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
2N5401	TO-92	5000 Unit / Bulk	
2N5401RL1	TO-92	2000 Tape & Reel	
2N5401RLRA	TO-92	2000 Tape & Reel	
2N5401RLRAG	TO-92 (Pb-Free)	2000 Tape & Reel	
2N5401RLRM	TO-92	2000 Tape & Ammo Box	
2N5401ZL1	TO-92	2000 Tape & Ammo Box	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

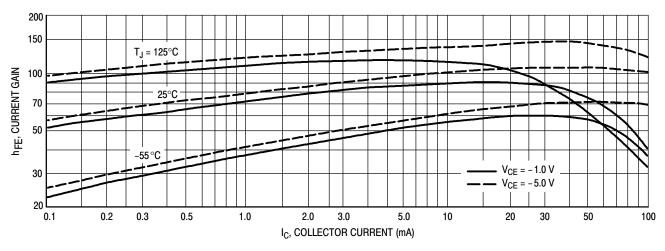


Figure 1. DC Current Gain

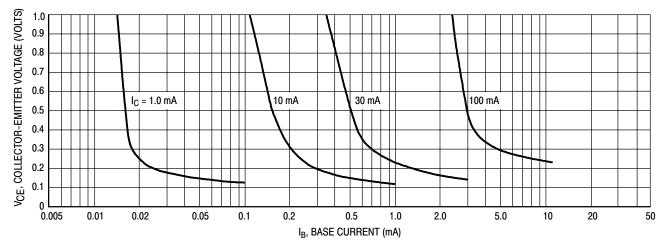


Figure 2. Collector Saturation Region

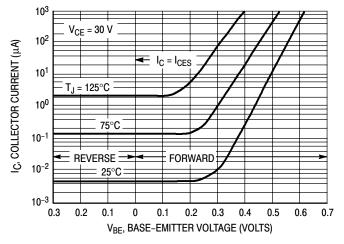


Figure 3. Collector Cut-Off Region

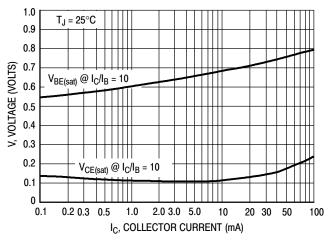
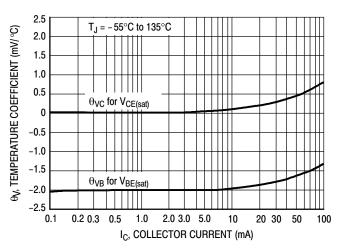
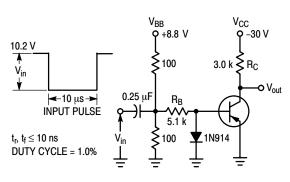


Figure 4. "On" Voltages



**Figure 5. Temperature Coefficients** 



Values Shown are for I<sub>C</sub> @ 10 mA

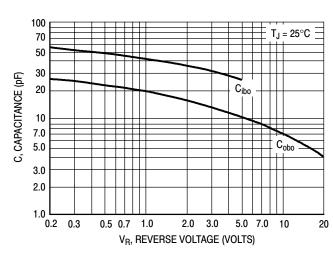
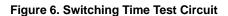


Figure 7. Capacitances



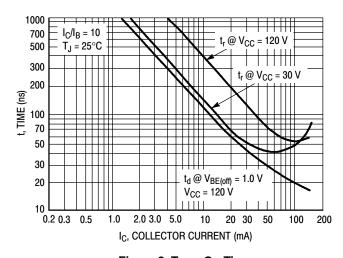


Figure 8. Turn-On Time

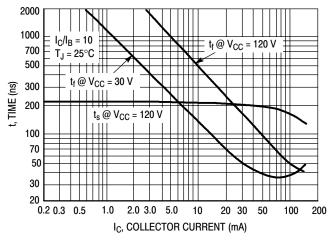
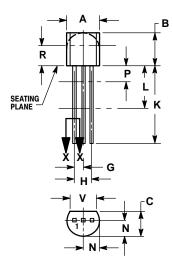


Figure 9. Turn-Off Time

# **PACKAGE DIMENSIONS**

TO-92 CASE 29-11 ISSUE AL





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

#### 2N5401

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